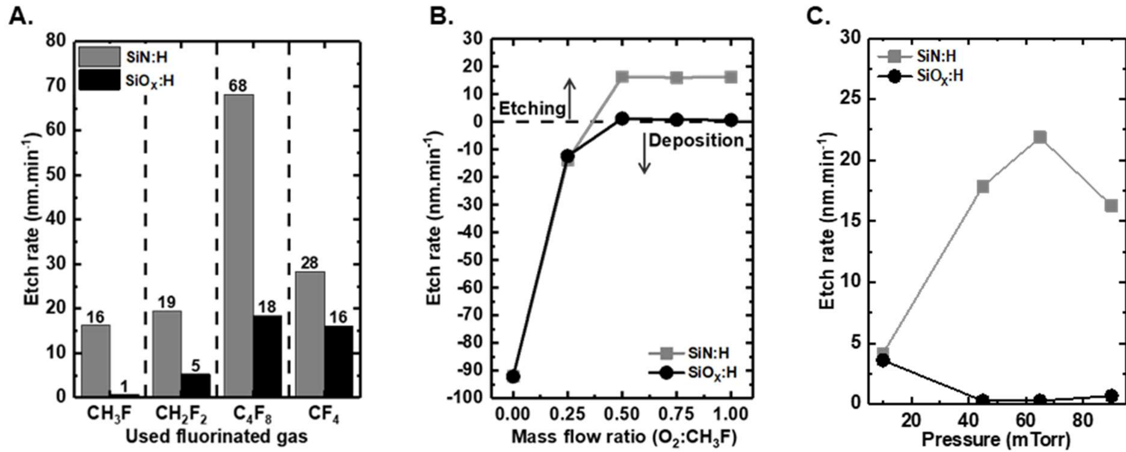

Fig. 1: Evolution of the etch rates as the function of **A.** the fluorinated gas at $O_2:C_XH_YF_Z = 1$ **B.** the $O_2:CH_3F$ ratio introduced in the feed gas and **C.** the operating pressure at $O_2:CH_3F = 1$. These data are obtained by spectroscopic ellipsometry (WOOLLAM M2000-DI).

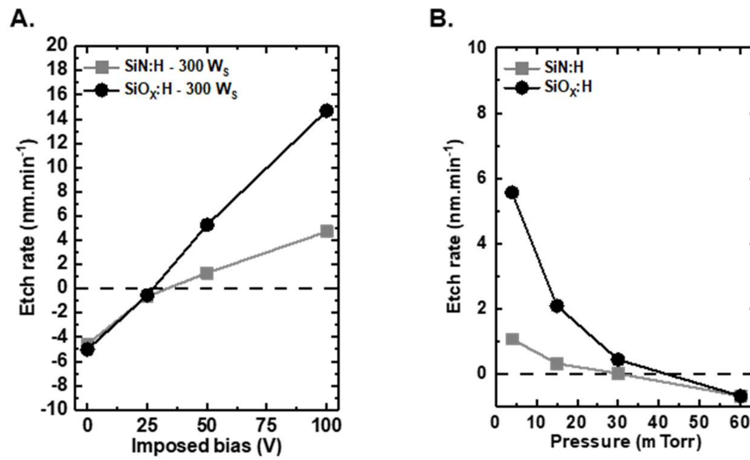

Fig. 2: Evolution of the etch rates as the function of **A.** the imposed bias voltage for BCl_3/Ar based process at 4 mTorr and **B.** operating pressure at a bias of 50 V. These data are obtained by spectroscopic ellipsometry (WOOLLAM M2000-DI).